

Application/Control Number: 10/743,814

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CLPTO

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1. A ferroelectric capacitor comprising:  
a pair of electrodes; and  
at least one ferroelectric held between the pair of electrodes,  
wherein the at least one ferroelectric comprises:  
a first ferroelectric layer having a surface roughness  
(RMS) determined with an atomic force microscope of 10 nm or  
more; and  
a second ferroelectric layer being arranged adjacent to  
the first ferroelectric layer and having a surface roughness (RMS)  
determined with an atomic force microscope of 5 nm or less.
2. A ferroelectric capacitor according to Claim 1, wherein  
the second ferroelectric layer is so arranged as to fill depressions on  
the surface of the first ferroelectric layer.
3. A ferroelectric capacitor according to Claim 1, wherein  
the first ferroelectric layer is formed at a temperature equal to or  
higher than a crystallization temperature at which the first  
ferroelectric layer takes on a crystalline structure displaying  
ferroelectricity, and wherein the second ferroelectric layer is formed  
at a temperature lower than a crystallization temperature at which  
the second ferroelectric layer takes on a crystalline structure  
displaying ferroelectricity.

4. A ferroelectric capacitor according to Claim 1, wherein the first ferroelectric layer is formed at a temperature equal to or higher than 500°C, and wherein the second ferroelectric layer is formed at a temperature lower than 500°C.

5. A ferroelectric capacitor according to Claim 1, wherein the first ferroelectric layer has a perovskite crystal structure and wherein the second ferroelectric layer has a perovskite crystal structure converted from an amorphous structure.

6. A ferroelectric capacitor according to Claim 5, wherein the second ferroelectric layer has a perovskite crystal structure converted from an amorphous structure as a result of a thermal treatment.

7. A ferroelectric capacitor according to Claim 6, wherein the thermal treatment is one of reduced-pressure rapid thermal annealing (RTA) at a temperature higher than the film forming temperature of the first ferroelectric layer and normal-pressure rapid thermal annealing (RTA) at a temperature higher than the film forming temperature of the first ferroelectric layer.

8. A ferroelectric capacitor according to Claim 1, wherein the ferroelectric is at least one selected from the group consisting of

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$\text{Pb}(\text{Zr,Ti})\text{O}_3$  [PZT],  $\text{SrBi}_2\text{Ta}_2\text{O}_9$  [SBT], and  $\text{Bi}_4\text{Ti}_3\text{O}_{12}$  [BIT].

9. A ferroelectric capacitor according to Claim 1, wherein the first ferroelectric layer comprises  $\text{Pb}(\text{Zr,Ti})\text{O}_3$  [PZT] having a perovskite crystal structure and wherein the second ferroelectric layer comprises  $\text{Pb}(\text{Zr,Ti})\text{O}_3$  [PZT] having a perovskite crystal structure converted from an amorphous structure.

10. A ferroelectric capacitor according to Claim 1, wherein the second ferroelectric has a perovskite crystal structure, except with its A-site doped with at least one selected from the group consisting of La, Sr, Ba and Ca.

11. A ferroelectric capacitor according to Claim 1, wherein the second ferroelectric has a perovskite crystal structure, except with its B-site doped with at least one selected from the group consisting of Nb, Ta, W and Bi.

12. A ferroelectric capacitor according to Claim 1, wherein at least one of the pair of electrodes comprises at least one selected from the group consisting of  $\text{IrO}_2$ ,  $\text{RuO}_2$ ,  $\text{SrRuO}_3$ , and  $\text{La}_{2-x}\text{Sr}_x\text{CuO}_4$ , wherein x is more than 0 and is 1 or less.

13. A ferroelectric capacitor according to Claim 1, comprising one of the pair of electrodes, the first ferroelectric layer,

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the second ferroelectric layer, and the other of the pair of electrodes in this order, wherein the first ferroelectric layer has columnar crystals, and wherein the second ferroelectric layer has granular crystals.

14. A semiconductor device comprising:

a substrate; and

a ferroelectric capacitor arranged above the substrate,

wherein the ferroelectric capacitor comprises:

a pair of electrodes; and

at least one ferroelectric held between the pair of electrodes,

wherein the at least one ferroelectric comprises:

a first ferroelectric layer having a surface roughness (RMS) determined with an atomic force microscope of 10 nm or more; and

a second ferroelectric layer being arranged adjacent to the first ferroelectric layer and having a surface roughness (RMS) determined with an atomic force microscope of 5 nm or less.

**CLAIMS 15-20 CANCELLED**